



## **RJK5012DPP-E0#T2 Information**



For Reference Only

Part Number RJK5012DPP-E0#T2

ManufacturerRenesas Electronics AmericaCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 500V 12A TO220

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









# **RJK5012DPP-E0#T2 Specifications**

Manufacturer Part Number         RJK5012DPP-E0#T2           Manufacturer         Renesas Electronics America           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3 Full Pack           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         12A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         29nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1100pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         620 mOhm @ 6A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220FP           Package / Case         TO-220-3 Full Pack		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Torin to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  12A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  1100pF @ 25V  Vgs (Max)  Vgs (Max)  TET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  MOSFET (Metal Oxide)  TO-220FP  Package / Case  TO-220FP  TO-220-3 Full Pack	Manufacturer Part Number	RJK5012DPP-E0#T2
Package         TO-220-3 Full Pack           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         500V           Current - Continuous Drain (Id) @ 25°C         12A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         29nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1100pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         30W (Tc)           Rds On (Max) @ Id, Vgs         620 mOhm @ 6A, 10V           Operating Temperature         150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220FP           Package / Case         TO-220-3 Full Pack	Manufacturer	Renesas Electronics America
Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case Toure	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case Took 100 mos FET Feature TO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 500V Current - Continuous Drain (Id) @ 25°C 12A (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs 29nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1100pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package 70-220FP Package / Case 170-220-5 Full Pack	Package	TO-220-3 Full Pack
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  12A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  500V  MOSFET (Metal Oxide)  500V  500V  500V  500V  500V  12A (Ta)	Series	-
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  12A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Supplier Device Package  Package / Case  500V  12A (Ta)  10V  10V  10V  10V	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  10V  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  620 mOhm @ 6A, 10V  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  Package / Case  12A (Ta)  10V  10V  110V  10V	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  10V	Drain to Source Voltage (Vdss)	500V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Ags On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  TO-220FP  Package / Case  Package / Case  29nC @ 10V  1100pF @ 25V  ±30V  FET Ge 25V  **  **  **  **  **  **  **  **  **	Current - Continuous Drain (Id) @ 25°C	12A (Ta)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Mounting Type  Through Hole  Supplier Device Package  TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  620 mOhm @ 6A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220FP  Package / Case  TO-220-3 Full Pack	Vgs(th) (Max) @ Id	-
Vgs (Max) ±30V  FET Feature -  Power Dissipation (Max) 30W (Tc)  Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V  Operating Temperature 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220FP  Package / Case TO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	29nC @ 10V
FET Feature - Gover Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	1100pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  620 mOhm @ 6A, 10V  Operating Temperature  150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220FP  Package / Case  TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs 620 mOhm @ 6A, 10V Operating Temperature 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	FET Feature	-
Operating Temperature 150°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220FP  Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	30W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	620 mOhm @ 6A, 10V
Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Operating Temperature	150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220FP
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

### **RJK5012DPP-E0#T2 Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### RJK5012DPP-E0#T2 Payment Methods



















## **RJK5012DPP-E0#T2 Shipping Methods**













If you have any question about RJK5012DPP-E0#T2, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com